

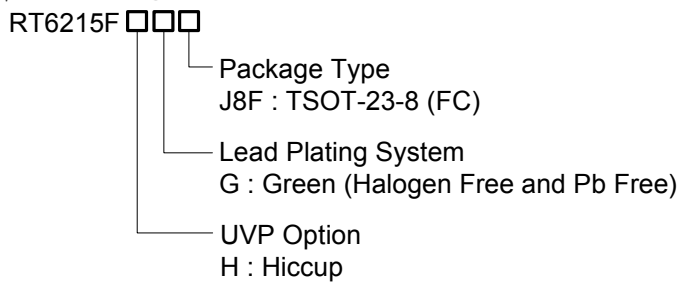
2A, 24V, 800kHz, ACOT™ Step-Down Converter

General Description

The RT6215F is a high-efficiency, synchronous step-down DC-DC converter that can deliver up to 2A output current from a 4.5V to 24V input supply. The RT6215F adopts Advanced Constant On-Time (ACOT™) control architecture to provide an ultrafast transient response with few external components and to operate in nearly constant switching frequency over line, load, and output voltage ranges.

The RT6215F features cycle-by-cycle current limit protection against short-circuit outputs, and soft-start function to prevent inrush current during start-up. It also includes input under-voltage lockout, output under-voltage protection, over-current protection, and over-temperature protection (thermal shutdown) to provide safe and smooth operation in all operating conditions.

Ordering Information



Note :

Richtek products are :

- ▶ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- ▶ Suitable for use in SnPb or Pb-free soldering processes.

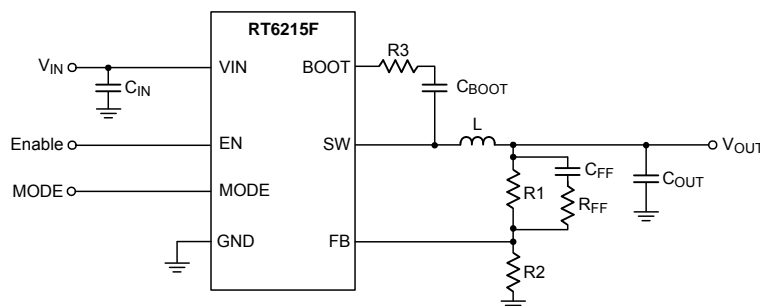
Features

- Input Supply Voltage Range : 4.5V to 24V
- Output Current : 2A
- Internal 100mΩ Switch and 85mΩ Synchronous Rectifier
- Advanced Constant On-Time (ACOT™) Control for Ultrafast Transient Response
- Steady Switching Frequency : 800kHz
- Optimized for Low-ESR Ceramic Output Capacitors
- 0.791V ±1.5% High-Accuracy Feedback Reference Voltage
- Programmable Output Voltage : 0.791V to 6V
- Monotonic Start-up for Pre-Biased Outputs
- Enable Control
- Cycle-by-Cycle Current Limit Protection
- Input Under-Voltage Lockout (UVLO)
- Output Under-Voltage Protection (UVP) with Hiccup Mode
- Over-Temperature Protection (OTP) (Thermal Shutdown)
- Available in TSOT-23-8 (FC) Package

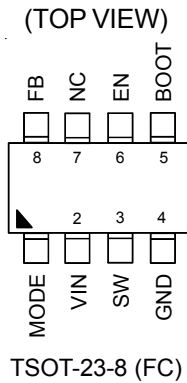
Applications

- Set Top Box
- Portable TV
- Access Point Router
- DSL Modem
- LCD TV

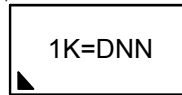
Simplified Application Circuit



Pin Configuration



Marking Information



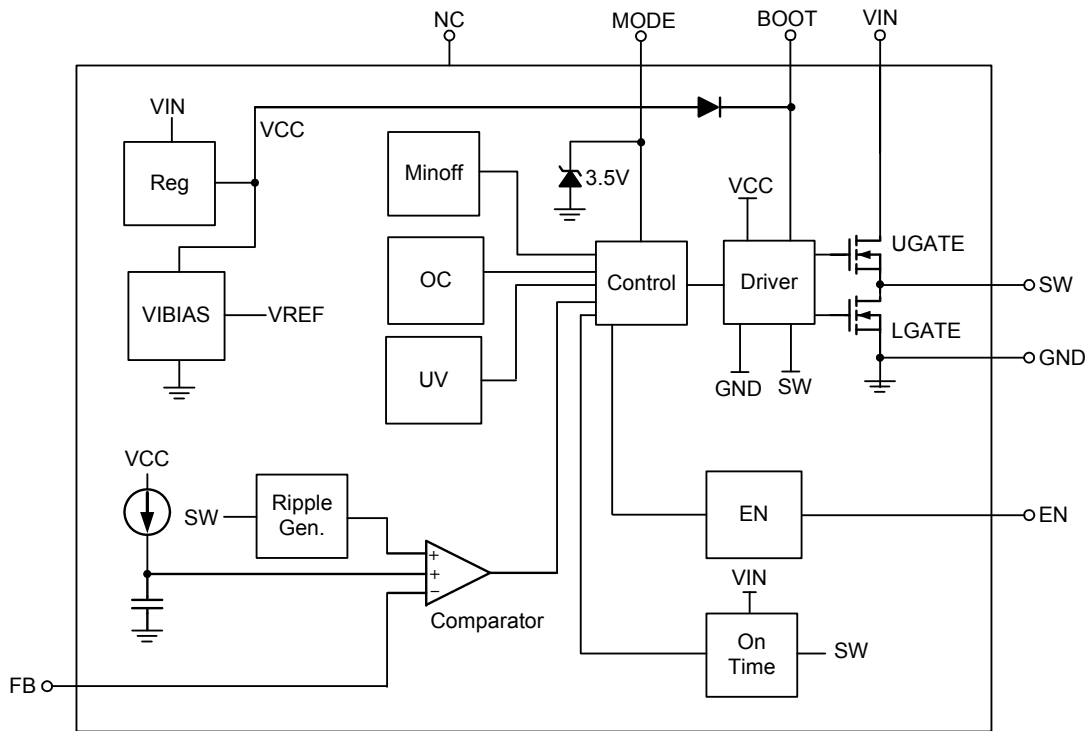
1K= : Product Code

DNN : Date Code

Functional Pin Description

Pin No.	Pin Name	Pin Function
1	MODE	Mode selection input. The RT6215F is forced into CCM by setting MODE pin high. Connect MODE to VIN with a 100kΩ resistor for CCM applications. Connecting the MODE pin to ground will enable power saving mode (PSM) at light load. Do not leave this pin unconnected.
2	VIN	Power input. The input voltage range is from 4.5V to 24V. Connect a suitable input capacitor between this pin and GND.
3	SW	Switch node between the internal switch and the synchronous rectifier. Connect this pin to the inductor and bootstrap capacitor.
4	GND	Power ground.
5	BOOT	Bootstrap capacitor connection node to supply the high-side gate driver. Connect a 0.1μF ceramic capacitor between this pin and SW pin.
6	EN	Enable control input. A logic-high enables the converter; a logic-low forces the device into shutdown mode.
7	NC	This pin is left to float.
8	FB	Feedback voltage input. Connect this pin to the midpoint of the external feedback resistive divider to set the output voltage of the converter to the desired regulation level. The device regulates the FB voltage at Feedback Threshold Voltage, typically 0.791V.

Functional Block Diagram



Operation

The RT6215F is a high-efficiency, synchronous step-down DC-DC converter that can deliver up to 2A output current from a 4.5V to 24V input supply. The RT6215F adopts ACOT™ control mode, which can reduce the output capacitance and provide ultrafast transient responses, and allow minimal components sizes without any additional external compensation network.

Enable Control

The RT6215F provides an EN pin, as an external chip enable control, to enable or disable the device. If V_{EN} is held below a logic-low threshold voltage (V_{ENL}) of the enable input (EN), the converter will enter into shutdown mode, that is, the converter is disabled and switching is inhibited even if the V_{IN} voltage is above V_{IN} under-voltage lockout threshold (V_{UVLO}). During shutdown mode, the supply current can be reduced to 10 μ A or below (I_{SHDN}). If the EN voltage rises above the logic-high threshold voltage (V_{ENH}) while the V_{IN} voltage is higher than UVLO threshold (V_{UVLO}), the device will be turned on, that is, switching being enabled and soft-start sequence being initiated.

Input Under-Voltage Lockout

In addition to the EN pin, the RT6215F also provides enable control through the V_{IN} pin. It features an under-voltage lockout (UVLO) function that monitors the internal linear regulator (VCC). If V_{EN} rises above V_{ENH} first, switching will still be inhibited until the V_{IN} voltage rises above V_{UVLO} . It is to ensure that the internal regulator is ready so that operation without fully-enhanced internal MOSFET switches can be prevented. After the device is powered up, if the input voltage V_{IN} goes below the UVLO-falling threshold voltage ($V_{UVLO} - \Delta V_{UVLO}$), this switching will be inhibited; if V_{IN} rises above the UVLO-rising threshold (V_{UVLO}), the device will resume switching.

Low-Side Current Limit Protection

The RT6215F features cycle-by-cycle valley-type current limit protection, measuring the inductor current through the synchronous rectifier (low-side switch). The inductor current level is determined by measuring the low-side switch voltage between the SW pin and GND, which is proportional to the switch current, during the low-side on-

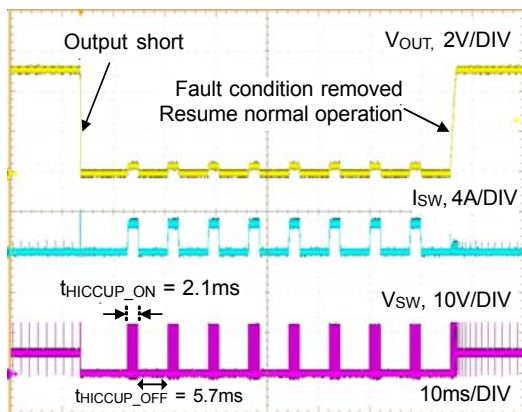
time. For greater accuracy, temperature compensation is added to the voltage sensing. Once the current rises above the low-side switch valley current limit (I_{LIM_L}), the on-time one-shot will be inhibited until the inductor current ramps down to the current limit level (I_{LIM_L}), that is, another on-time can only be triggered when the inductor current goes below the low-side current limit. This function can prevent the average output current from greatly exceeding the guaranteed low-side current limit value. If the output load current exceeds the available inductor current (clamped by the above-mentioned low-side current limit), the output capacitor needs to supply the extra current such that the output voltage will begin to drop. If it drops below the output under-voltage protection trip threshold, the IC will stop switching to avoid excessive heat.

Output Under-Voltage Protection

The RT6215F includes output under-voltage protection (UVP) against over-load or short-circuited condition by constantly monitoring the feedback voltage V_{FB} . If V_{FB} drops below the under-voltage protection trip threshold (typically 50% of the internal reference voltage), the UV comparator will go high to turn off both the internal high-side and low-side MOSFET switches.

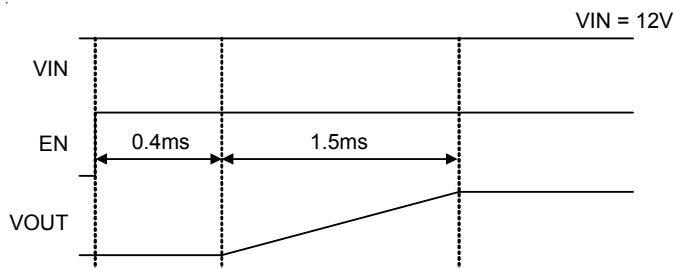
Hiccup Mode

If the output under-voltage condition continues for a period of time, the RT6215F will enter output under-voltage protection with hiccup mode. During hiccup mode, the IC will shut down for t_{HICCUP_OFF} (5.7ms), and then attempt to recover automatically for t_{HICCUP_ON} (2.1ms). Upon completion of the soft-start sequence, if the fault condition is removed, the converter will resume normal operation; otherwise, such cycle for auto-recovery will be repeated until the fault condition is cleared. Hiccup mode allows the circuit to operate safely with low input current and power dissipation, and then resume normal operation as soon as the over-load or short-circuit condition is removed.



Soft-Start (SS)

The RT6215F provides an internal soft-start feature for inrush control. At power up, the internal capacitor is charged by an internal current source to generate a soft-start ramp voltage as a reference voltage to the PWM comparator. The device will initiate switching and the output voltage will smoothly ramp up to its targeted regulation voltage only after this ramp voltage is greater than the feedback voltage V_{FB} to ensure the converters have a smooth start-up. The output voltage starts to rise in 0.4ms from EN rising, and the soft-start ramp-up time (V_{FB} from 0V to 0.791V) is 1.5ms.



External Bootstrap Capacitor

Connect a 0.1 μ F low-ESR ceramic capacitor between the BOOT and SW pins. This bootstrap capacitor supplies for the gate driver of the high-side N-channel MOSFET switch.

Over-Temperature Protection (Thermal Shutdown)

The RT6215F includes an over-temperature protection (OTP) circuitry to prevent overheating due to excessive power dissipation. The OTP will shut down switching operation when junction temperature exceeds a thermal shutdown threshold T_{SD} . Once the junction temperature cools down by a thermal shutdown hysteresis (ΔT_{SD}), the IC will resume normal operation with a complete soft-start.

Absolute Maximum Ratings (Note 1)

- Supply Input Voltage and EN Voltage, V_{IN} , EN ----- -0.3V to 28V
- Switch Voltage, SW ----- -0.3V to 28V
 SW ($t \leq 10\text{ns}$) ----- -5V to 30V
- BOOT to SW, $V_{BOOT} - V_{SW}$ ----- -0.3V to 6V
- BOOT Voltage ----- -0.3V to 34V
- Other Pins ----- -0.3V to 6V
- Power Dissipation, P_D @ $T_A = 25^\circ\text{C}$
 TSOT-23-8 (FC) ----- 1.428W
- Package Thermal Resistance (Note 2)
 TSOT-23-8 (FC), θ_{JA} ----- 70°C/W
 TSOT-23-8 (FC), θ_{JC} ----- 15°C/W
- Junction Temperature ----- 150°C
- Lead Temperature (Soldering, 10 sec.) ----- 260°C
- Storage Temperature Range ----- -65°C to 150°C
- ESD Susceptibility (Note 3)
 HBM (Human Body Model) ----- 2kV

Recommended Operating Conditions (Note 4)

- Supply Input Voltage ----- 4.5V to 24V
- Junction Temperature Range ----- -40°C to 125°C
- Ambient Temperature Range ----- -40°C to 85°C

Electrical Characteristics

($V_{IN} = 12\text{V}$, $T_A = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Supply Voltage						
VIN Supply Input Operating Voltage	V_{IN}		4.5	--	24	V
VIN Under-Voltage Lockout Threshold	V_{UVLO}	V_{IN} rising	3.9	4.1	4.3	V
VIN Under-Voltage Lockout Threshold-Hysteresis	ΔV_{UVLO}		--	550	--	mV
Supply Current						
Supply Current (Shutdown)	I_{SHDN}	$V_{EN} = 0\text{V}$	--	--	10	μA
Supply Current (Quiescent)	I_Q	$V_{EN} = 2\text{V}$, $V_{FB} = 1\text{V}$	--	170	270	μA
Soft-Start						
Internal Soft-Start Period	t_{SS}	V_{FB} from 0% to 100%	--	1500	--	μs
Enable Voltage						
EN Rising Threshold	V_{ENH}		1.2	1.4	1.6	V
EN Falling Threshold	V_{ENL}		1.1	1.25	1.4	V
Mode Input Voltage						
Mode Input High Voltage	V_{MODEH}		2	--	--	V
Mode Input Low Voltage	V_{MODEL}		--	--	0.4	V

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Feedback Voltage						
Feedback Threshold Voltage	V _{TH_FB}		779	791	803	mV
Internal MOSFET						
High-Side Switch-On Resistance	R _{DS(ON)_H}	V _{BOOT} -V _{SW} = 4.8V	--	100	--	mΩ
Low-Side Switch-On Resistance	R _{DS(ON)_L}		--	85	--	mΩ
Current Limit						
Low-Side Switch Valley Current Limit	I _{LIM_L}		2.2	2.7	--	A
High-Side Switch Peak Current Limit	I _{LIM_H}		--	5	--	A
Switching Frequency						
Switching Frequency	f _{SW}		--	800	--	kHz
On-Time Timer Control						
Maximum Duty Cycle	D _{MAX}		--	84	--	%
Minimum On-Time	t _{ON_MIN}		--	60	--	ns
Thermal Shutdown						
Thermal Shutdown	T _{SD}		--	160	--	°C
Thermal Hysteresis	ΔT _{SD}		--	25	--	°C
Output Under Voltage Protections						
UVP Trip Threshold		UVP detected	--	50	--	%
		Hysteresis	--	10	--	%

Note 1. Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Note 2. θ_{JA} is measured under natural convection (still air) at T_A = 25°C with the component mounted on a high effective-thermal-conductivity four-layer test board on a JEDEC 51-7 thermal measurement standard. The first layer is filled with copper. θ_{JC} is measured at the lead of the package.

Note 3. Devices are ESD sensitive. Handling precaution is recommended.

Note 4. The device is not guaranteed to function outside its operating conditions.

Typical Application Circuit

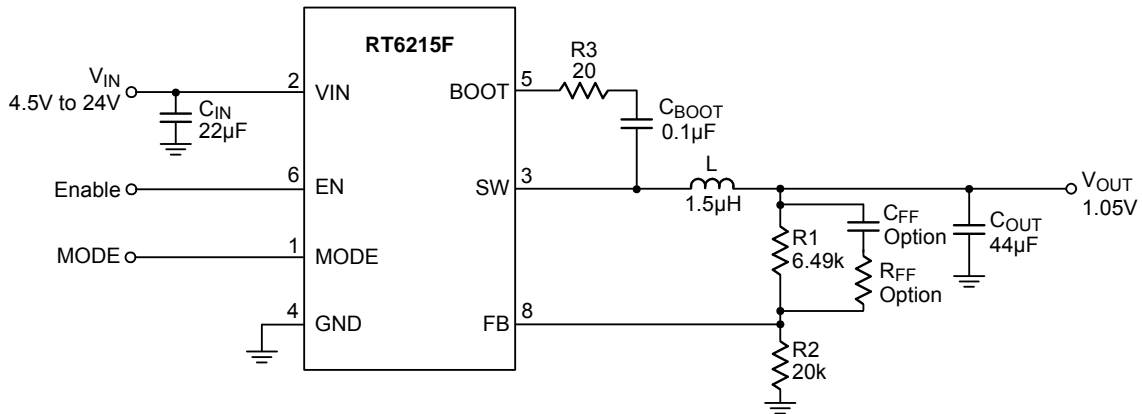


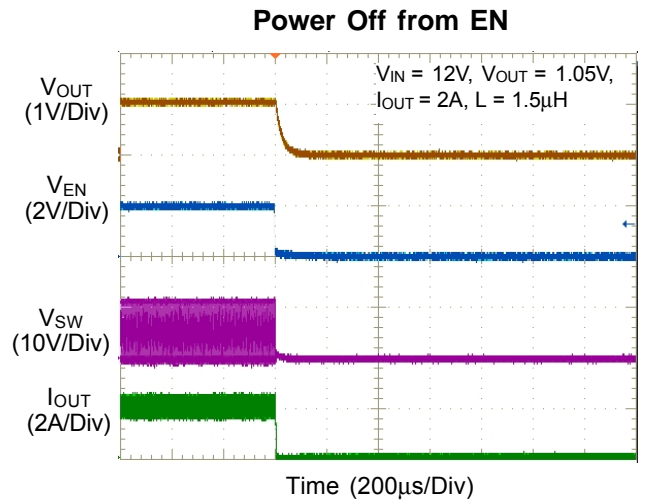
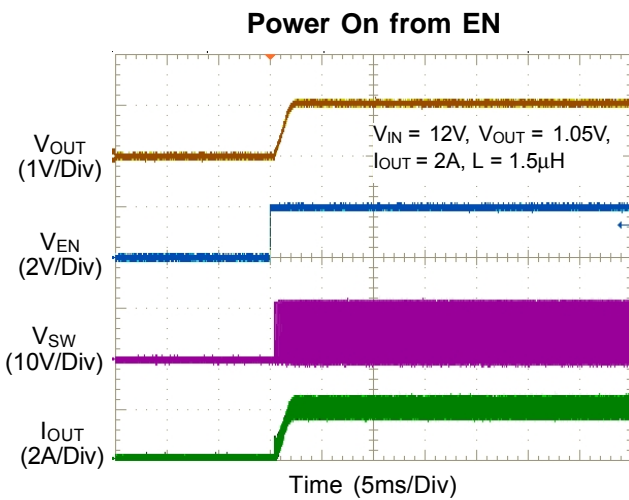
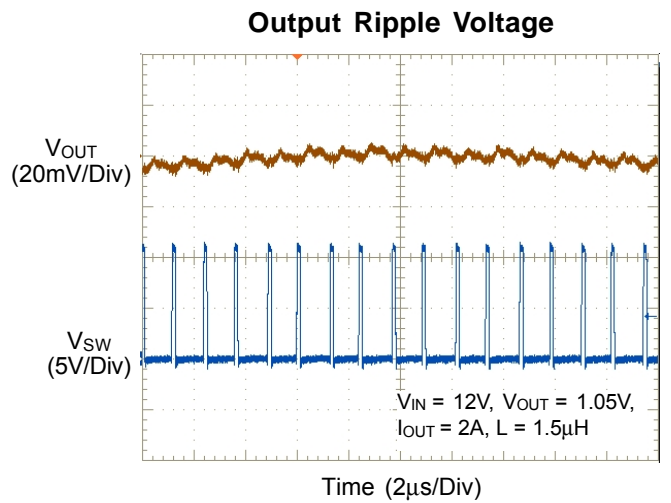
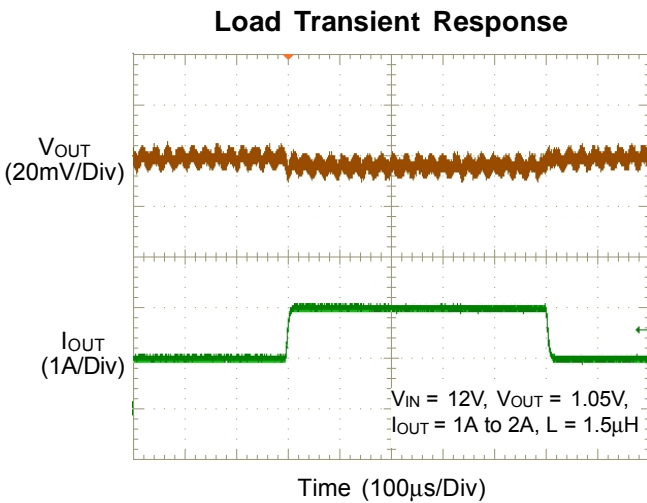
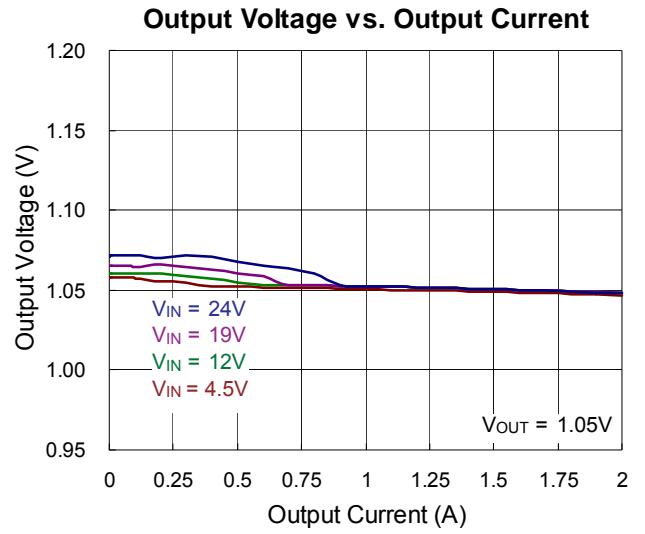
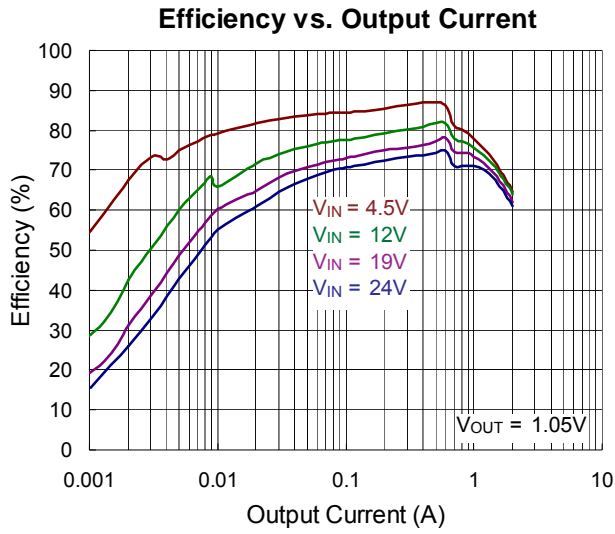
Table 1. Suggested Component Values

V _{OUT} (V)	R ₁ (kΩ)	R ₂ (kΩ)	L (µH)	C _{OUT} (µF)	C _{FF} (pF)	R _{FF} (kΩ)
1.05	6.49	20	1.5	44	--	--
1.2	10.5	20	1.8	44	--	--
1.8	25.5	20	2.2	44	--	--
2.5	43.2	20	2.8	44	22 to 68	20, when C _{FF} ≥ 47pF
3.3	63.4	20	3.6	44	22 to 68	20, when C _{FF} ≥ 47pF
5	107	20	4.7	44	22 to 68	20, when C _{FF} ≥ 47pF

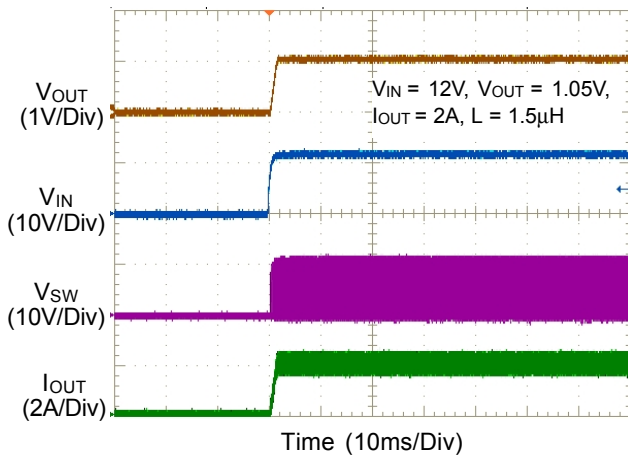
Note :

- (1) All the input and output capacitors are the suggested values, referring to the effective capacitances, subject to any de-rating effect, like a DC bias.
- (2) For lower output voltage applications, load transient responses can also be improved by adding a feedforward capacitor (C_{FF}, 22pF to 68pF).

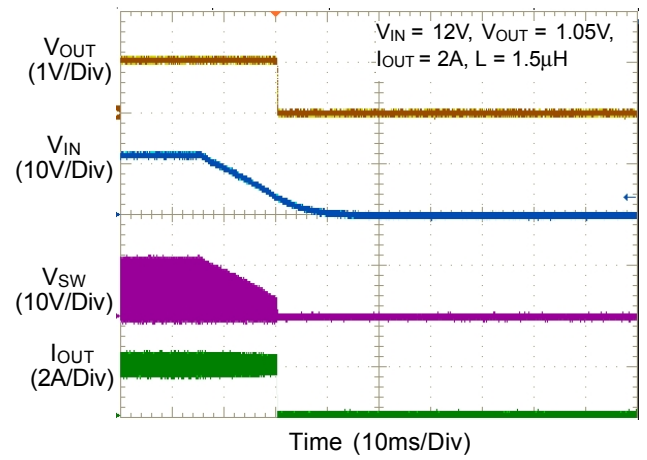
Typical Operating Characteristics



Power On from VIN



Power Off from VIN



Application Information

Inductor Selection

When designing the output stage of the synchronous buck converter, it is recommended to start with the inductor. However, it may require several iterations because the exact inductor value is generally flexible and is optimized for low cost, small form factor, and high overall performance of the converter. Further, inductors vary with manufacturers in both material and value, and typically have a tolerance of $\pm 20\%$.

Three key inductor parameters to be specified for operation with the device are inductance (L), inductor saturation current (I_{SAT}), and DC resistance (DCR), which affects performance of the output stage. An inductor with lower DCR is recommended for applications of higher peak current or load current, and it can improve system performance. Lower inductor values are beneficial to the system in physical size, cost, DCR, and transient response, but they will cause higher inductor peak current and output voltage ripple to decrease system efficiency. Conversely, higher inductor values can increase system efficiency at the expense of larger physical size, slower transient response due to the longer response time of the inductor. A good compromise among size, efficiency, and transient response can be achieved by setting an inductor current ripple (ΔI_L) of about 20% to 50% of the desired full output load current. To meet the inductor current ripple (ΔI_L) requirements, a minimum inductance must be chosen and the approximate inductance can be calculated by the selected input voltage, output voltage, switching frequency (f_{SW}), and inductor current ripple (ΔI_L), as below :

$$L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times \Delta I_L}$$

Once the inductance is chosen, the inductor ripple current (ΔI_L) and peak inductor current (I_{L_PEAK}) can be calculated, as below :

$$\Delta I_L = \frac{V_{OUT} \times (V_{IN} - V_{OUT})}{V_{IN} \times f_{SW} \times L}$$

$$I_{L_PEAK} = I_{OUT_MAX} + \frac{1}{2} \Delta I_L$$

$$I_{L_VALLY} = I_{OUT_MAX} - \frac{1}{2} \Delta I_L$$

where I_{OUT_MAX} is the maximum rated output current or the required peak current.

The inductor must be selected to have a saturation current and thermal rating which exceed the required peak inductor current I_{L_PEAK} . For a robust design to maintain control of inductor current in overload or short-circuit conditions, some applications may desire inductor saturation current rating up to the high-side switch current limit of the device. However, the built-in output under-voltage protection (UVP) feature makes this unnecessary for most applications.

I_{L_PEAK} should not exceed the minimum value of the device's high-side switch current limit because the device will not be able to supply the desired output current. By reducing the inductor current ripple (ΔI_L) to increase the average inductor current (and the output current), I_{L_PEAK} can be lowered to meet the device current limit requirement.

For best efficiency, a low-loss inductor having the lowest possible DCR that still fits in the allotted dimensions will be chosen. Ferrite cores are often the best choice. However, a shielded inductor, possibly larger or more expensive, will probably give fewer EMI and other noise problems.

The following design example is illustrated to walk through the steps to apply the equations defined above. The RT6215F's Typical Application Circuit for output voltage of 1.05V at maximum output current of 2A and an input voltage of 12V with inductor current ripple of 0.8A (i.e. 40%, in the recommended range of 20% to 50%, of the maximum rated output current) is taken as the design example. The approximate minimum inductor value can first be calculated as below :

$$L = \frac{1.05 \times (12 - 1.05)}{12 \times 800\text{kHz} \times 0.8\text{A}} = 1.49\mu\text{H}$$

where f_{SW} is 800kHz. The inductor current ripple will be set at 0.8A, as long as the calculated inductance of 1.49 μ H is used. However, the inductor of the exact inductance value may not be readily available, and therefore an inductor of a nearby value will be chosen. In this case, 1.5 μ H inductance is available and actually used in the Typical

Application Circuit. The actual inductor current ripple (ΔI_L) and required peak inductor current (I_{L_PEAK}) can be calculated as below :

$$\Delta I_L = \frac{1.05 \times (12 - 1.05)}{12 \times 800 \text{kHz} \times 1.5 \mu\text{H}} = 0.8 \text{A}$$

$$I_{L_PEAK} = I_{OUT_MAX} + \frac{1}{2} \Delta I_L = 2 + \frac{0.8}{2} = 2.4 \text{A}$$

For the 1.5 μ H inductance value, the inductor saturation current and thermal rating should exceed 2.4A.

Input Capacitor Selection

Input capacitors are needed to smooth out the RMS ripple current (I_{RMS}) imposed by the switching currents and drawn from the input power source, by reducing the ripple voltage amplitude seen at the input of the converters. The voltage rating of the input filter capacitors must be greater than the maximum input voltage. It's also important to consider the ripple current capabilities of capacitors.

The RMS ripple current (I_{RMS}) of the regulator can be determined by the input voltage (V_{IN}), output voltage (V_{OUT}), and rated output current (I_{OUT}) as the following equation :

$$I_{RMS} = I_{OUT} \times \frac{V_{OUT}}{V_{IN}} \times \sqrt{\frac{V_{IN}}{V_{OUT}} - 1}$$

From the above, the maximum RMS input ripple current occurs at maximum output load, which will be used as the requirements to consider the current capabilities of the input capacitors. Furthermore, for a single phase buck converter, the duty cycle is approximately the ratio of output voltage to input voltage. The maximum ripple voltage usually occurs at 50% duty cycle, that is, $V_{IN} = 2 \times V_{OUT}$. The maximum I_{RMS} , as $I_{RMS} (Max)$, can be approximated as $0.5 \times I_{OUT_MAX}$, where I_{OUT_MAX} is the maximum rated output current. Besides, the variation of the capacitance value with temperature, DC bias voltage, switching frequency, and allowable peak-to-peak ripple voltage that reflects back to the input, also need to be taken into consideration. For example, the capacitance value of a capacitor decreases as the DC bias across the capacitor increases; also, higher switching frequency allows the use of input capacitors of smaller capacitance values.

Ceramic capacitors are most commonly used to be placed right at the input of the converter to reduce ripple voltage

amplitude because only ceramic capacitors have extremely low ESR which is required to reduce the ripple voltage. Note that the capacitors need to be placed as close as to the input pins as possible for highest effectiveness. Ceramic capacitors are preferred also due to their low cost, small size, high RMS current ratings, robust inrush surge current capabilities, and low parasitic inductance, which helps reduce the high-frequency ringing on the input supply.

However, care must be taken when ceramic capacitors are used at the input, and the input power is supplied by a wall adapter, connected through a long and thin wire. When a load step occurs at the output, a sudden inrush current will surge through the long inductive wire, which can induce ringing at the device's power input and potentially cause a very large voltage spike at the VIN pin to damage the device. For applications where the input power is located far from the device input, it may be required that the low-ESR ceramic input capacitors be placed in parallel with a bulk capacitor of other types, such as tantalum, electrolytic, or polymer, to dampen the voltage ringing and overshoot at the input, caused by the long input power path and input ceramic capacitor.

It is suggested to choose capacitors with higher temperature ratings than required. Several ceramic capacitors may be parallel to meet application requirements, such as the RMS current, size, and height. The Typical Application Circuit can use one 22 μ F, or two 10 μ F and one high-frequency- noise-filtering 0.1 μ F low-ESR ceramic capacitors at the input.

Output Capacitor Selection

Output capacitance affects the output voltage of the converter, the response time of the output feedback loop, and the requirements for output voltage sag and soar. The sag occurs after a sudden load step current applied, and the soar occurs after a sudden load removal. Increasing the output capacitance reduces the output voltage ripple and output sag and soar, while it increases the response time that the output voltage feedback loop takes to respond to step loads. Therefore, there is a tradeoff between output capacitance and output response. It is recommended to choose a minimum output capacitance to meet the output voltage requirements of the converter, and have a quick

transient response to step loads.

The ESR of the output capacitor affects the damping of the output filter and the transient response. In general, low-ESR capacitors are good choices due to their excellent capability in energy storage and transient performance. The RT6215F, therefore, is specially optimized for ceramic capacitors. Consider also DC bias and aging effects while selecting the output capacitor.

● **Output Voltage Ripple**

The output voltage ripple at the switching frequency is a function of the inductor current ripple going through the output capacitor’s impedance. To derive the output voltage ripple, the output capacitor with capacitance, C_{OUT} , and its equivalent series resistance, R_{ESR} , must be taken into consideration. The output peak-to-peak ripple voltage ΔV_{P-P} , caused by the inductor current ripple ΔI_L , is characterized by two components, which are ESR ripple ΔV_{P-P_ESR} and capacitive ripple ΔV_{P-P_C} , can be expressed as below :

$$\Delta V_{P-P} = \Delta V_{P-P_ESR} + \Delta V_{P-P_C}$$

$$\Delta V_{P-P_ESR} = \Delta I_L \times R_{ESR}$$

$$\Delta V_{P-P_C} = \frac{\Delta I_L}{8 \times C_{OUT} \times f_{SW}}$$

If ceramic capacitors are used as the output capacitors, both the components need to be considered due to the extremely low ESR and relatively small capacitance.

● **Output Transient Undershoot and Overshoot**

In addition to the output voltage ripple at the switching frequency, the output capacitor and its ESR also affect output voltage sag, which is undershoot on a positive load step, and output voltage soar, which is overshoot on a negative load step. With the built-in ACOT™ architecture, the IC can have very fast transient responses to the load steps and small output transients.

However, the combination of a small ceramic output capacitor (that is, of little capacitance) and a low output voltage (that is, only little charge stored in the output capacitor), used in low-duty-cycle applications (which require high inductance to get reasonable ripple currents for high input voltages), causes an increase in the size of voltage variations (i.e. sag/soar) in response to very

quick load changes. Typically, the load changes slowly, compared with the IC’s switching frequency. However, for present-day applications, more and more digital blocks may exhibit nearly instantaneous large transient load changes. Therefore, in the following section, how to calculate the worst-case voltage swings in response to very fast load steps will be explained in details.

Both of the output transient undershoot and overshoot have two components : a voltage step caused by the output capacitor’s ESR, and a voltage sag or soar due to the finite output capacitance and the inductor current slew rate. The following formulas can be used to check if the ESR is low enough (which is usually not a problem with ceramic capacitors) and if the output capacitance is large enough to prevent excessive sag or soar on very fast load steps, with the chosen inductor value.

The voltage step (ΔV_{OUT_ESR}) caused by the ESR is a function of the load step (ΔI_{OUT}) and the ESR (R_{ESR}) of the output capacitor, described as below :

$$\Delta V_{OUT_ESR} = \Delta I_{OUT} \times R_{ESR}$$

The voltage amplitude (ΔV_{OUT_SAG}) of the capacitive sag is a function of the load step (ΔI_{OUT}), the output capacitor value (C_{OUT}), the inductor value (L), the input-to-output voltage differential, and the maximum duty cycle (D_{MAX}). And, the maximum duty cycle during a fast transient can be determined by the on-time (t_{ON}) and the minimum off-time (t_{OFF_MIN}) since the ACOT™ control scheme will ramp the current during on-times, which are spaced apart by a minimum off-time, that is, as fast as allowed. The approximate on-time (neglecting parasitics) and maximum duty cycle for a given input and output voltage can be calculated according to the following equations :

$$t_{ON} = \frac{V_{OUT}}{V_{IN} \times f_{SW}} \text{ and } D_{MAX} = \frac{t_{ON}}{t_{ON} + t_{OFF_MIN}}$$

Note the actual on-time will be slightly larger than the calculated one as the IC will automatically adapt to compensate the internal voltage drops, such as the voltage across high-side switch due to on-resistance. However, both of these can be neglected since the on-time increase can compensate for the voltage drops. The output voltage sag (ΔV_{OUT_SAG}) can then be calculated as below :

$$\Delta V_{OUT_SAG} = \frac{L \times (\Delta I_{OUT})^2}{2 \times C_{OUT} \times (V_{IN} \times D_{MAX} - V_{OUT})}$$

The voltage amplitude of the capacitive soar is a function of the load step (ΔI_{OUT}), the output capacitor value (C_{OUT}), the inductor value (L), and the output voltage (V_{OUT}). And the output voltage soar (ΔV_{OUT_SOAR}) can be calculated as below :

$$\Delta V_{OUT_SOAR} = \frac{L \times (\Delta I_{OUT})^2}{2 \times C_{OUT} \times V_{OUT}}$$

Feedforward Capacitor (C_{FF})

The RT6215F is optimized for ceramic output capacitors and for low duty-cycle applications. This optimization makes circuit stability easy to achieve with reasonable output capacitors, but it also narrows the optimization of transient responses of the converter. For high output voltage (that is, high duty-cycle) applications, the FB voltage is highly attenuated from the output, the circuit's response becomes under-damped and transient response is slowed. A small feedforward capacitor (C_{FF}) can be introduced into the feedback network to speed up the transient response of high output voltage circuits. The feedforward capacitor is added across the upper FB divider resistor (as seen in Figure 1) to speed up the transient response without affecting the steady-state stability of the circuit.

To optimize transient response, a C_{FF} value is chosen so that the gain and phase boost of the feedback network increases the bandwidth of the converter, while still maintaining an acceptable phase margin. Generally, larger C_{FF} values provide higher bandwidth, but may result in an unacceptable phase margin or instability. Suitable feedforward capacitor values can be chosen from the table of Suggested Component Values.

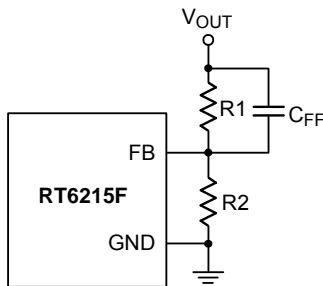


Figure 1. C_{FF} Capacitor Setting

EN Pin for Start-Up and Shutdown Operation

For automatic start-up, the EN pin, with high voltage rating, can be connected to the input supply V_{IN} , through a 100k Ω resistor. The large built-in hysteresis band makes the EN pin useful for simple delay and timing circuits. The EN pin can be externally connected to V_{IN} by adding a resistor R_{EN} and a capacitor C_{EN} , as shown in Figure 2, to have an additional delay. The time delay can be calculated with the EN's internal threshold, at which switching operation begins (typically 1.4V).

An external MOSFET can be added for the EN pin to be logic-controlled, as shown in Figure 3. In this case, a 100k Ω pull-up resistor, R_{EN} , is connected between V_{IN} and the EN pin. The MOSFET Q1 will be under logic control to pull down the EN pin. To prevent the device being enabled when V_{IN} is smaller than the V_{OUT} target level or some other desired voltage level, a resistive divider (R_{EN1} and R_{EN2}) can be used to externally set the input under-voltage lockout threshold, as shown in Figure 4.

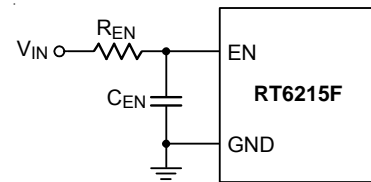


Figure 2. Enable Timing Control

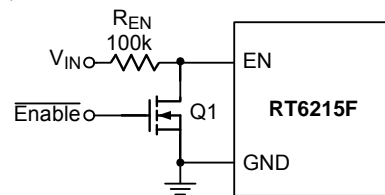


Figure 3. Logic Control for the EN Pin

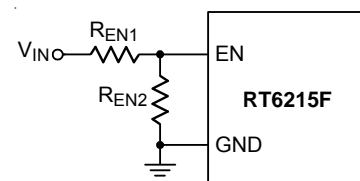


Figure 4. Resistor Divider for Under-Voltage Lockout Threshold Setting

Output Voltage Setting

The output voltage can be programmed by a resistive divider from the output to ground with the midpoint connected to the FB pin. The resistive divider allows the FB pin to sense a fraction of the output voltage as shown in Figure 5. The output voltage is set according to the following equation :

$$V_{OUT} = V_{TH_FB} \times (1 + \frac{R1}{R2}) + \frac{1}{2} \Delta V_{OUT_P-P}$$

where V_{TH_FB} is around 0.791V (Typ).

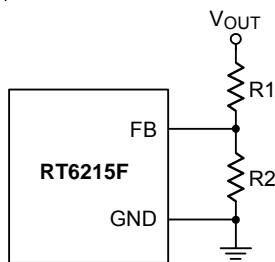


Figure 5. Output Voltage Setting

The placement of the resistive divider should be within 5mm of the FB pin. The resistance of R2 is suggested between 10kΩ and 100kΩ to minimize power consumption and noise pick-up at the FB pin. Once R2 is chosen, the resistance of R1 can then be obtained as below :

$$R1 = \frac{R2 \times (V_{OUT} - V_{TH_FB})}{V_{TH_FB}}$$

For better output voltage accuracy, the divider resistors (R1 and R2) with ±1% tolerance or better should be used.

External Bootstrap Diode

A bootstrap capacitor of 0.1μF low-ESR ceramic capacitor is connected between the BOOT and SW pins to supply the high-side gate driver. It is recommended to add an external bootstrap diode between an external 5V voltage supply and the BOOT pin to improve enhancement of the internal MOSFET switch and improve efficiency when the input voltage is below 5.5V. The bootstrap diode can be a low-cost one, such as 1N4148 or BAT54. The external 5V can be a fixed 5V voltage supply from the system, or a 5V output voltage generated by the RT6215F. Note that the BOOT voltage V_{BOOT} must be lower than 5.5V.

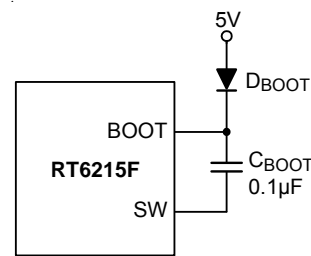


Figure 6. External Bootstrap Diode

Resistor at BOOT Pin

The gate driver of an internal power MOSFET, utilized as a high-side switch, is optimized for turning on the switch not only fast enough for reducing switching power loss, but also slow enough for minimizing EMI. The EMI issue is worse when the switch is turned on rapidly due to high di/dt noises induced. When the high-side switch is being turned off, the SW node will be discharged relatively slowly by the inductor current due to the presence of the dead time when both the high-side and low-side switches are turned off.

In some cases, it is desirable to reduce EMI further, even at the expense of some additional power dissipation. The turn-on rate of the high-side switch can be slowed by placing a small (< 47Ω) resistor between the BOOT pin and the external bootstrap capacitor. This will slow down the rates of the high-side switch turn-on and the rise of V_{SW} . The recommended application circuit is shown in Figure 7, which includes an external bootstrap diode for charging the bootstrap capacitor and a bootstrap resistor R_{BOOT} being placed between the BOOT pin and the capacitor/diode connection.

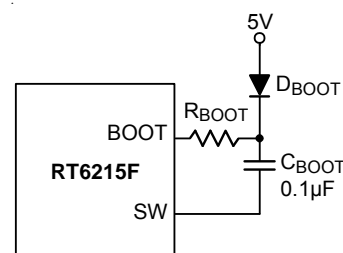


Figure 7. External Bootstrap Diode and Resistor at the BOOT Pin

Mode Selection Setting

The RT6215F provide the MODE pin to set Power Saving Mode (PSM) for light load. To connect the MODE pin to ground allows the RT6215F to enter Power Saving Mode for light load efficiency enhancement. Pulling the MODE pin high (i.e. > 2V) will force the RT6215F to enter CCM. In order to avoid abnormal operation caused by noise, the MODE pin should not be floated.

Thermal Considerations

The junction temperature should never exceed the absolute maximum junction temperature $T_{J(MAX)}$, listed under Absolute Maximum Ratings, to avoid permanent damage to the device. The maximum allowable power dissipation depends on the thermal resistance of the IC package, the PCB layout, the rate of surrounding airflow, and the difference between the junction and ambient temperatures. The maximum power dissipation can be calculated using the following formula :

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction-to-ambient thermal resistance.

For continuous operation, the maximum operating junction temperature indicated under Recommended Operating Conditions is 125°C. The junction-to-ambient thermal resistance, θ_{JA} , is highly package dependent. For a TSOT-23-8 (FC) package, the thermal resistance, θ_{JA} , is 70°C/W on a standard JEDEC 51-7 high effective-thermal-conductivity four-layer test board. The maximum power dissipation at $T_A = 25^\circ\text{C}$ can be calculated as below :

$$P_{D(MAX)} = (125^\circ\text{C} - 25^\circ\text{C}) / (70^\circ\text{C}/\text{W}) = 1.428\text{W for a TSOT-23-8 (FC) package.}$$

The maximum power dissipation depends on the operating ambient temperature for the fixed $T_{J(MAX)}$ and the thermal resistance, θ_{JA} . The derating curves in Figure 8 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

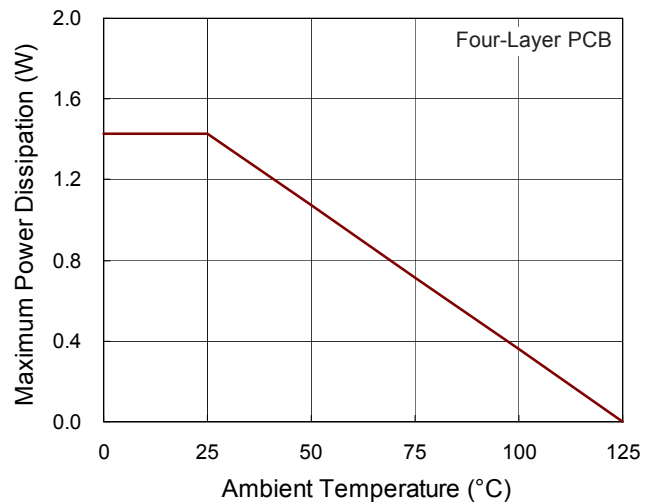


Figure 8. Derating Curve of Maximum Power Dissipation

Layout Considerations

Follow the PCB layout guidelines for optimal performance of the device.

- ▶ Keep the high-current paths short, especially at the ground terminals. This practice is essential for stable, jitter-free operation. The high current path comprising of input capacitor, high-side FET, inductor, and the output capacitor should be as short as possible. This practice is essential for high efficiency.
- ▶ Place the input MLCC capacitors as close to the VIN and GND pins as possible. The major MLCC capacitors should be placed on the same layer as the RT6215F.
- ▶ SW node is with high frequency voltage swing and should be kept at small area. Keep analog components away from the SW node to prevent stray capacitive noise pickup.
- ▶ Connect feedback network behind the output capacitors. Place the feedback components next to the FB pin.
- ▶ For better thermal performance, to design a wide and thick plane for GND pin or to add a lot of vias to GND plane.

An example of PCB layout guide is shown from Figure 9.

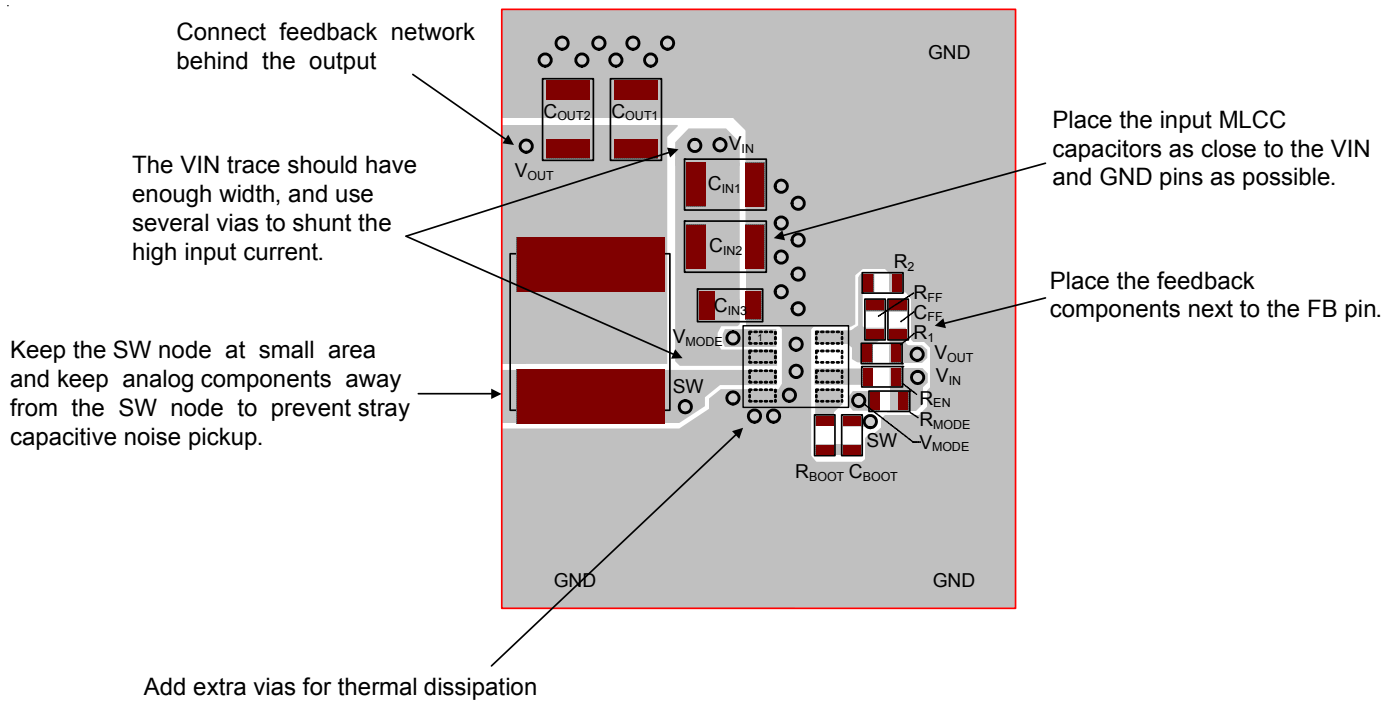
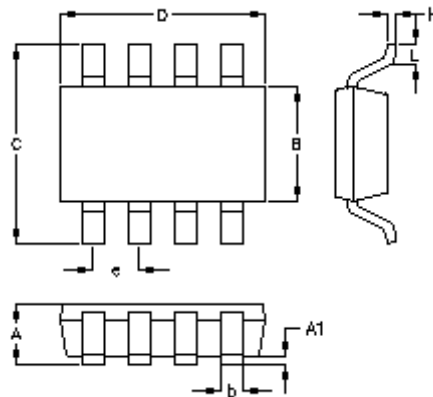


Figure 9. PCB Layout Guide

Outline Dimension



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	1.000	0.028	0.039
A1	0.000	0.100	0.000	0.004
B	1.397	1.803	0.055	0.071
b	0.220	0.380	0.009	0.015
C	2.591	3.000	0.102	0.118
D	2.692	3.099	0.106	0.122
e	0.585	0.715	0.023	0.028
H	0.080	0.254	0.003	0.010
L	0.300	0.610	0.012	0.024

TSOT-23-8 (FC) Surface Mount Package

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